

HiPerFET™ Power MOSFETs

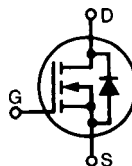
IXFX 50N50
IXFX 55N50

V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	50 A	100 mΩ
500 V	55 A	80 mΩ

$t_{rr} \leq 250$ ns

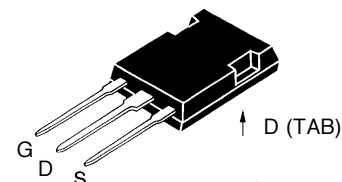
Single Die MOSFET

Preliminary data sheet



Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V	
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ MΩ	500	V	
V_{GS}	Continuous	±20	V	
V_{GSM}	Transient	±30	V	
I_{D25}	$T_C = 25^\circ\text{C}$	50N50	50	A
		55N50	55	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	50N50	200	A
		55N50	220	A
I_{AR}	$T_C = 25^\circ\text{C}$	50N50	50	A
		55N50	55	A
E_{AR}	$T_C = 25^\circ\text{C}$	60	mJ	
E_{AS}	$T_C = 25^\circ\text{C}$	3	J	
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/μs, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	V/ns	
P_D	$T_C = 25^\circ\text{C}$	520	W	
T_J		-55 ... +150	$^\circ\text{C}$	
T_{JM}		150	$^\circ\text{C}$	
T_{stg}		-55 ... +150	$^\circ\text{C}$	
T_L	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ\text{C}$	
M_d	Mounting torque	1.13/10	Nm/lb.in.	
Weight		6	g	

**PLUS247™
(IXFX)**



Features

- International standard package
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

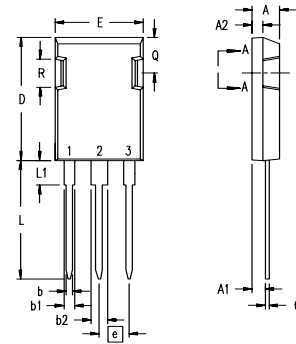
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 1$ mA	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8$ mA	2.5		V
I_{GSS}	$V_{GS} = \pm 20$ V, $V_{DS} = 0$			±200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		25 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5$ I_{D25} Note 1	50N50 55N50		100 mΩ 80 mΩ

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$ Note 1		45	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9400	pF
C_{oss}			1280	pF
C_{rss}			460	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ (External),		45	ns
t_r			60	ns
$t_{d(off)}$			120	ns
t_f			45	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		330	nC
Q_{gs}			55	nC
Q_{gd}			155	nC
R_{thJC}			0.22	K/W
R_{thCK}			0.15	K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	55N50 50N50		55 A 50 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	55N50 50N50		220 A 200 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$ Note 1			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
Q_{RM}			1.0	μC
I_{RM}			10	A

Note: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

PLUS 247™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Figure 1. Output Characteristics at 25°C

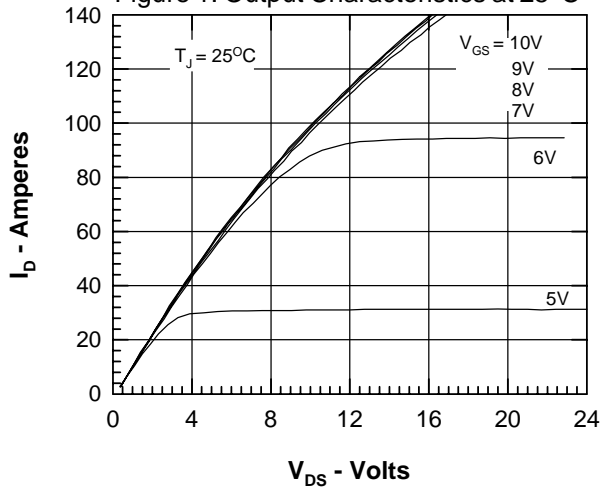


Figure 2. Output Characteristics at 125°C

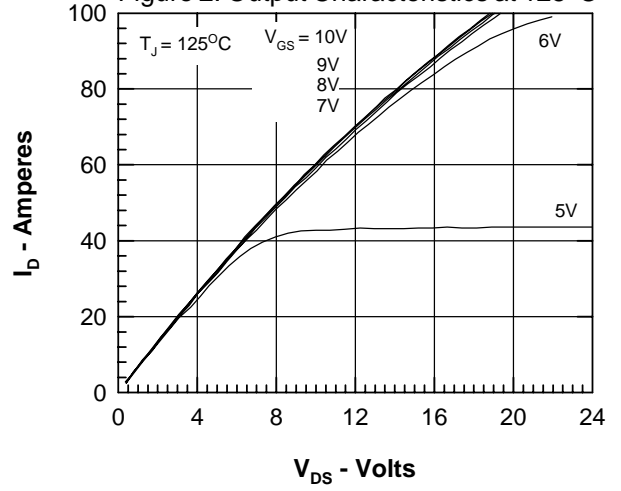


Figure 3. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. I_D

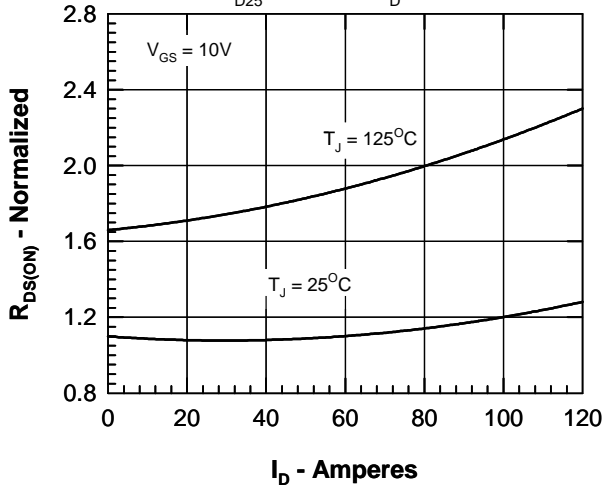


Figure 4. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. T_J

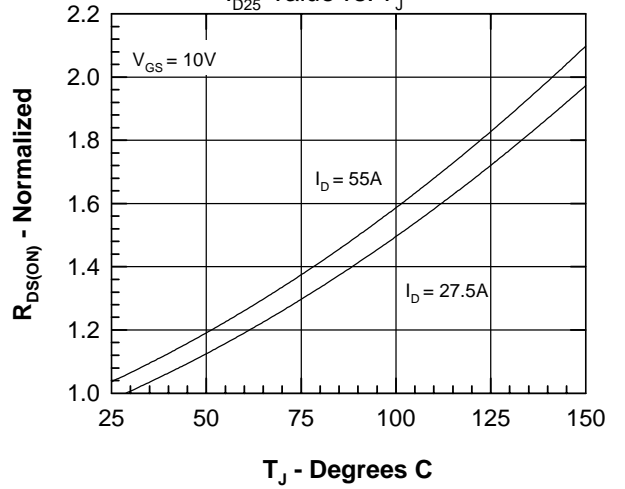


Figure 5. Drain Current vs. Case Temperature

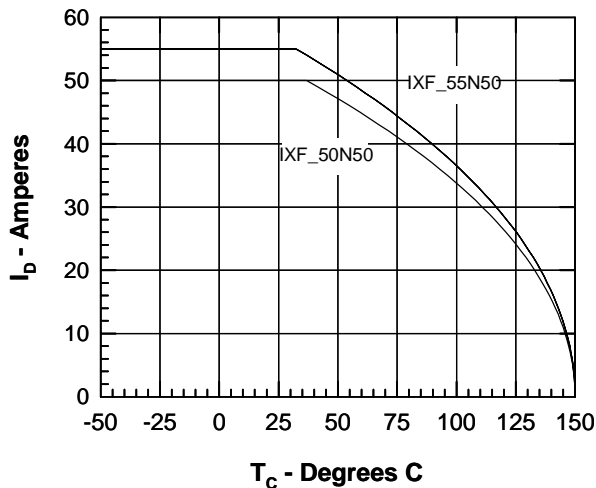


Figure 6. Admittance Curves

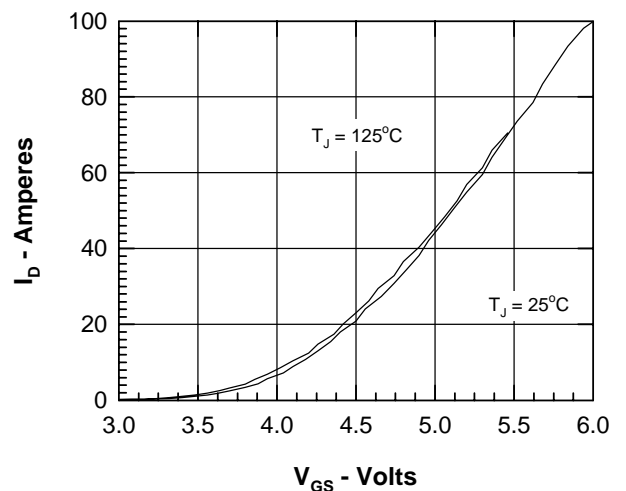


Figure 7. Gate Charge

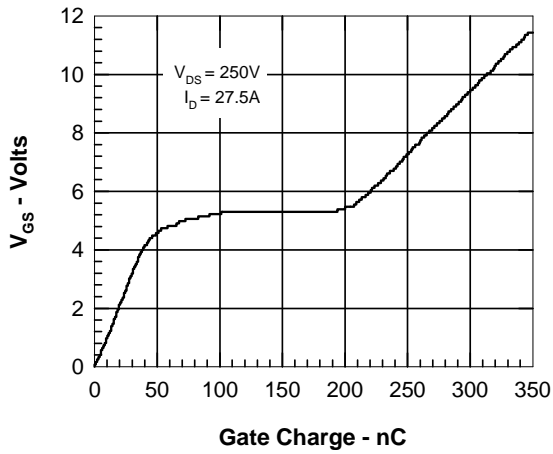


Figure 8. Capacitance Curves

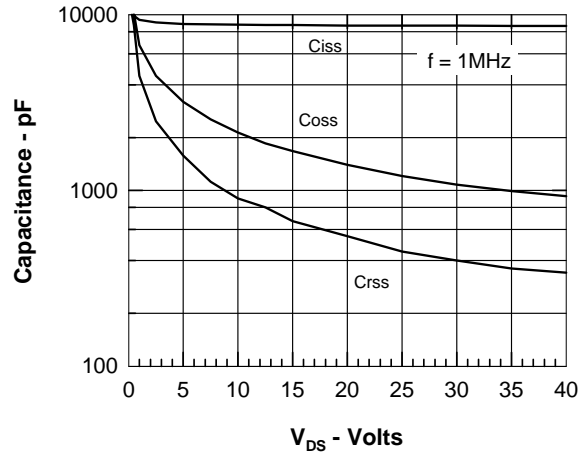


Figure 9. Forward Voltage Drop of the Intrinsic Diode

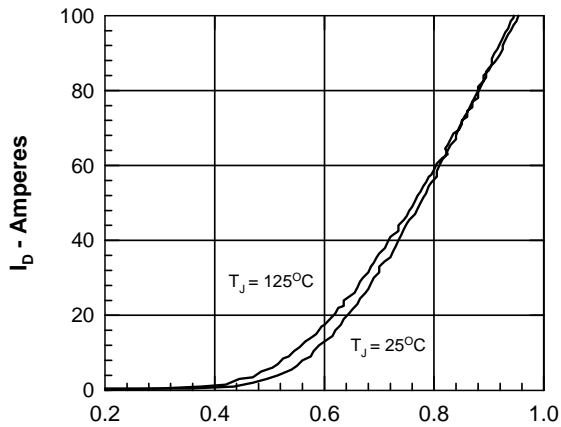
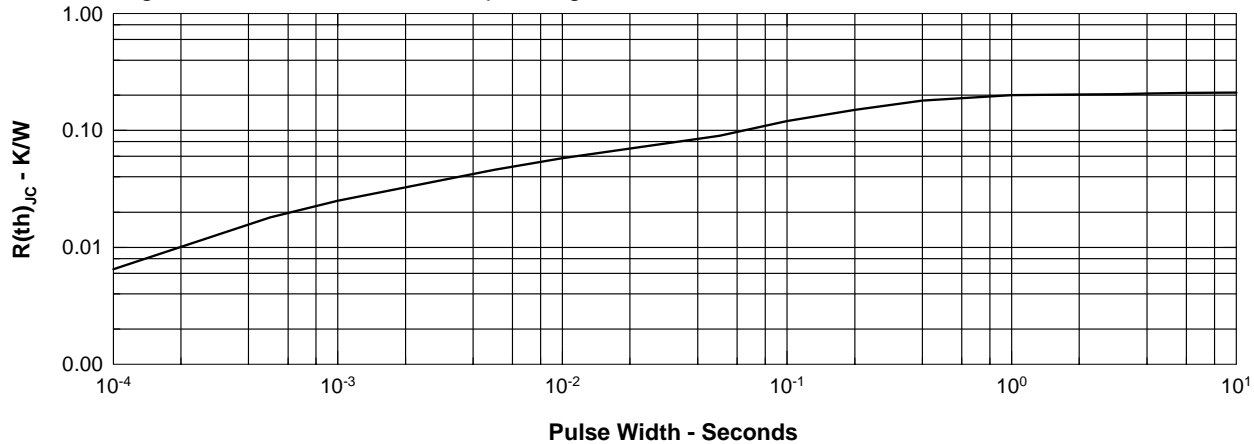


Figure 10. Forward Bias Safe Operating Area



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	